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BCP56

WT.MO; BCP56

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SOT-223 1004.0

NPN General Purpose Amplifier

W.100X.COM.TW These devices are designed for general purpose medium power amplifiers and switches requiring collector WWW.100Y.C currents to 1A. Sourced from Process 39.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

currents to 1A. Sourced from Process 39. Absolute Maximum Ratings* TA = 25°C unless otherwise noted					
Symbol	Parameter	BCP56	Units		
V _{CEO}	Collector-Emitter Voltage	80	CON .		
V _{CBO}	Collector-Base Voltage	100	V		
V _{EBO}	Emitter-Base Voltage	5 W.10	VOV V		
lc	Collector Current - Continuous	1.2	A		
T _{J,} T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C		

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

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W.100Y.COM.T 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations. UWW.I

Symbol	Characteristic	Max	Units
		BCP56	WWW
P _D	Total Device Dissipation Derate above 25°C		W mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient	125	°C/W
*Device mou	inted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector	lead min. 6 cm².	N N

Thermal Characteristics

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NPN General Purpose Amplifier (continued)						
	Test Conditions	Min	Max	Unit		
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Collector-Emitter Breakdown Voltage	lc = 10 mA	80		V		
Collector-Base Breakdown Voltage		100	N	V		
Emitter-Base Breakdown Voltage	Ι _E = 10 μΑ	5	W	V		
Collector Cutoff Current	V _{CB} = 30 V V _{CB} = 30 V, T _i = +125°C	COM	100 10	nA uA		
Emitter Cutoff Current	V _{EB} = 5V	N.COM	10	μA		
IEBO Emitter Cuton Current VEB = 5V 10 μA ON CHARACTERISTICS*						
DC Current Gain	$I_{C} = 5 \text{ mA}, V_{CE} = 2V$ $I_{C} = 150 \text{ mA}, V_{CE} = 2V$ $I_{C} = 500\text{mA}, V_{CE} = 2 V$	25 40 25	250	- 17 17 17 17 17		
Collector-Emitter Saturation Voltage	I _C = 500 m A, I _B = 50 mA	100	0.5	V		
Base-Emitter On Voltage	I _C = 500 m A, V _{CE} = 2 V	W.10	N.10	V		
	Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current Excremistics* DC Current Gain Collector-Emitter Saturation Voltage	T_A = 25°C unless otherwise noted Test Conditions Test Conditions RACTERISTICS Collector-Emitter Breakdown Voltage Ic = 10 mA Collector-Base Breakdown Voltage Ic = 100 μ A Emitter-Base Breakdown Voltage Ie = 10 μ A Collector Cutoff Current V _{CB} = 30 V V _{CB} = 30 V, T _J = +125°C V _{CB} = 30 V, T _J = +125°C Emitter Cutoff Current V _{EB} = 5V RACTERISTICS* DC Current Gain Ic = 5 mA, V _{CE} = 2V Ic = 150 mA, V _{CE} = 2V Ic = 500mA, V _{CE} = 2V Ic = 500 mA, V _{CE} = 2 V Ic = 500 mA, I _B = 50 mA	Parameter Test Conditions Min RACTERISTICS Collector-Emitter Breakdown Voltage Ic = 10 mA 80 Collector-Base Breakdown Voltage Ic = 100 μ A 100 Emitter-Base Breakdown Voltage Ic = 100 μ A 5 Collector Cutoff Current V _{CB} = 30 V V _{CB} = 30 V V _{CB} = 30 V, T _j = +125°C V 2 Emitter Cutoff Current V _{EB} = 5V V RACTERISTICS* DC Current Gain Ic = 5 mA, V _{CE} = 2V 25 Ic = 500 mA, V _{CE} = 2V 25 40 25 Collector-Emitter Saturation Voltage Ic = 500 m A, I _B = 50 mA 100	TA = 25°C unless otherwise notedParameterTest ConditionsMinMaxRACTERISTICSCollector-Emitter Breakdown Voltage $I_C = 10 \text{ mA}$ 80Collector-Base Breakdown Voltage $I_C = 100 \mu A$ 100Emitter-Base Breakdown Voltage $I_E = 10 \mu A$ 5Collector Cutoff Current $V_{CB} = 30 V$ 100Emitter Cutoff Current $V_{CB} = 30 V$ 100Collector Cutoff Current $V_{EB} = 5V$ 10RACTERISTICS*DC Current Gain $I_C = 5 \text{ mA}, V_{CE} = 2V$ $25 \\ 40 \\ 25 \end{bmatrix}$ DC Current Gain $I_C = 5 \text{ mA}, V_{CE} = 2V$ $25 \\ 40 \\ 25 \end{bmatrix}$ $250 \\ 250 \\ 1c = 500 \text{ mA}, V_{CE} = 2V \\ 1c = 500 \text{ mA}, V_{CE} = 2V \\ 1c = 500 \text{ mA}, V_{CE} = 2V \end{bmatrix}$ $25 \\ 40 \\ 25 \end{bmatrix}$		

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